

SPTECH Silicon PNP Power Transistor**2SA985****DESCRIPTION**

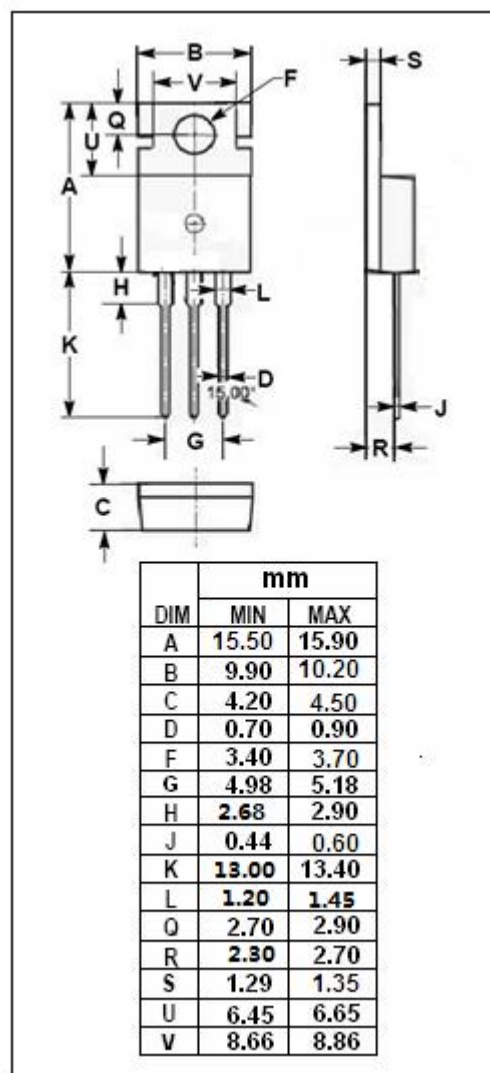
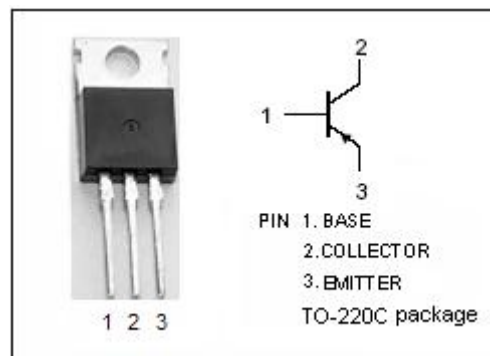
- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -120V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC2275

APPLICATIONS

- Audio frequency power amplifier applications
- High frequency power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-3.0	A
I_B	Base Current-Continuous	-0.3	A
P_C	Total Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Total Power Dissipation @ $T_c=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SA985****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -0.1A			-2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1A; I _B = -0.1A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V ; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3V; I _C = 0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -5mA ; V _{CE} = -5V	35			
h _{FE-2}	DC Current Gain	I _C = -0.3A ; V _{CE} = -5V	60		320	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		29		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.2A; V _{CE} = -5V		180		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320